

PRELIMINARY
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 Some parametric limits are subject to change.

MITSUBISHI Pch POWER MOSFET

FX3ASJ-3

HIGH-SPEED SWITCHING USE

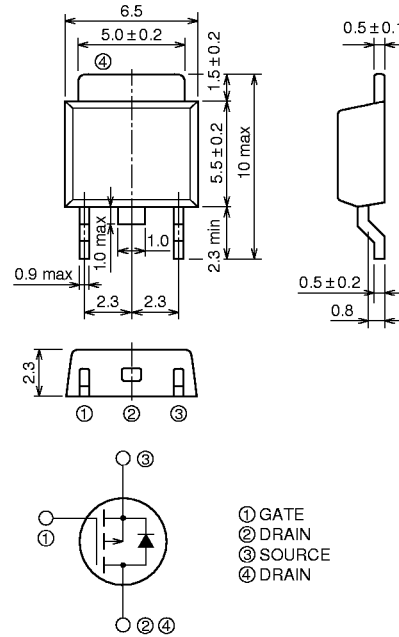
FX3ASJ-3



- 4V DRIVE
- V_{DSS} -150V
- $r_{DS(ON)}$ (MAX) 1.2Ω
- I_D -3A
- Integrated Fast Recovery Diode (TYP.) 80ns

OUTLINE DRAWING

Dimensions in mm



MP-3

APPLICATION

Motor control, Lamp control, Solenoid control
 DC-DC converter, etc.

MAXIMUM RATINGS (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DSS}	Drain-source voltage	$V_{GS} = 0V$	-150	V
V_{GSS}	Gate-source voltage	$V_{DS} = 0V$	± 20	V
I_D	Drain current		-3	A
I_{DM}	Drain current (Pulsed)		-12	A
I_{DA}	Avalanche drain current (Pulsed)	$L = 100\mu H$	-3	A
I_S	Source current		-3	A
I_{SM}	Source current (Pulsed)		-12	A
PD	Maximum power dissipation		30	W
T_{ch}	Channel temperature		-55 ~ +150	°C
T_{stg}	Storage temperature		-55 ~ +150	°C
—	Weight	Typical value	0.26	g

Jan.1999

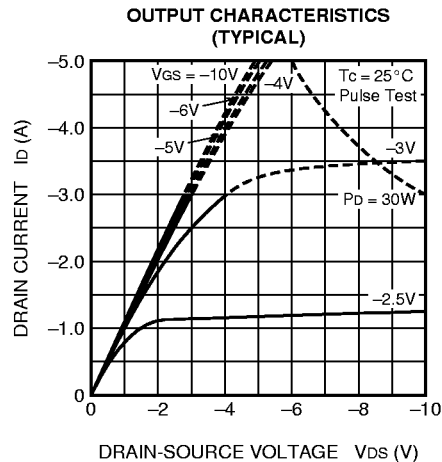
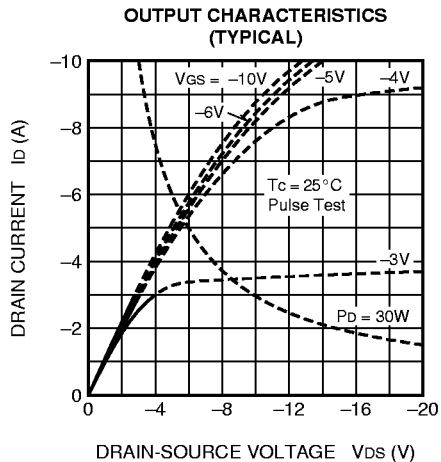
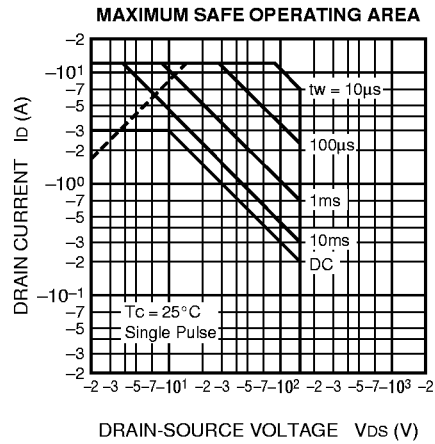
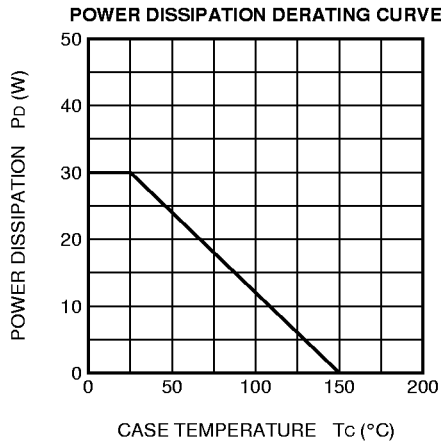


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ELECTRICAL CHARACTERISTICS ($T_{ch} = 25^{\circ}\text{C}$)

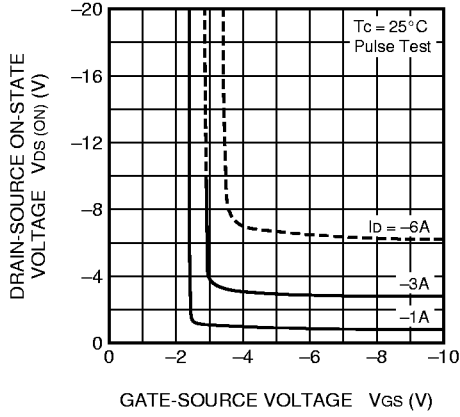
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V(BR)DSS	Drain-source breakdown voltage	$I_D = -1\text{mA}, V_{GS} = 0\text{V}$	-150	—	—	V
IGSS	Gate-source leakage current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$	—	—	± 0.1	μA
IDSS	Drain-source leakage current	$V_{DS} = -150\text{V}, V_{GS} = 0\text{V}$	—	—	-0.1	mA
VGS(th)	Gate-source threshold voltage	$I_D = -1\text{mA}, V_{DS} = -10\text{V}$	-1.0	-1.5	-2.0	V
rDS(ON)	Drain-source on-state resistance	$I_D = -1\text{A}, V_{GS} = -10\text{V}$	—	0.93	1.20	Ω
rDS(ON)	Drain-source on-state resistance	$I_D = -1\text{A}, V_{GS} = -4\text{V}$	—	1.02	1.32	Ω
VDS(ON)	Drain-source on-state voltage	$I_D = -1\text{A}, V_{GS} = -10\text{V}$	—	-0.93	-1.20	V
yfs	Forward transfer admittance	$I_D = -1\text{A}, V_{DS} = -5\text{V}$	—	3.0	—	S
Ciss	Input capacitance	$V_{DS} = -10\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$	—	1170	—	pF
Coss	Output capacitance		—	81	—	pF
Crss	Reverse transfer capacitance		—	31	—	pF
td(on)	Turn-on delay time	$V_{DD} = -80\text{V}, I_D = -1\text{A}, V_{GS} = -10\text{V}, R_{GEN} = R_{GS} = 50\Omega$	—	9	—	ns
tr	Rise time		—	7	—	ns
td(off)	Turn-off delay time		—	82	—	ns
tf	Fall time		—	33	—	ns
VSD	Source-drain voltage	$I_S = -1\text{A}, V_{GS} = 0\text{V}$	—	-1.0	-1.5	V
Rth(ch-c)	Thermal resistance	Channel to case	—	—	4.17	$^{\circ}\text{C/W}$
trr	Reverse recovery time	$I_S = -3\text{A}, \text{dis}/\text{dt} = 100\text{A}/\mu\text{s}$	—	80	—	ns

PERFORMANCE CURVES

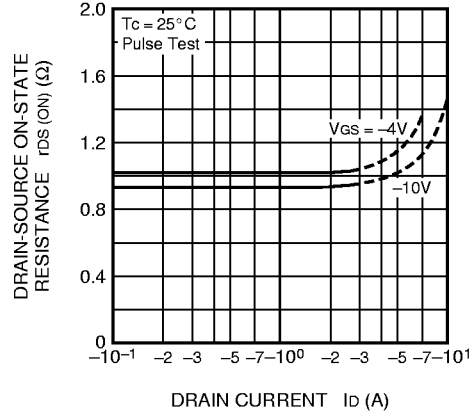


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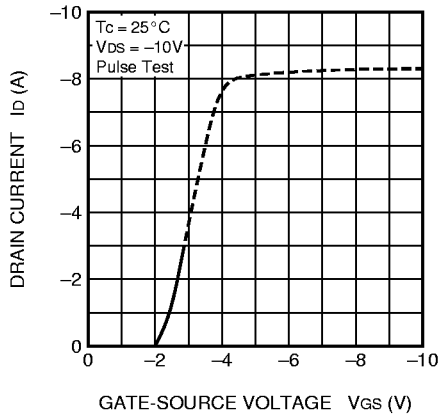
ON-STATE VOLTAGE VS. GATE-SOURCE VOLTAGE (TYPICAL)



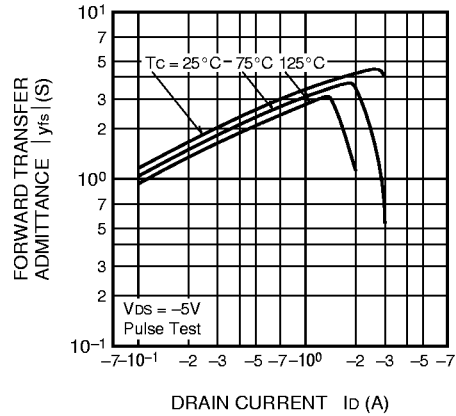
ON-STATE RESISTANCE VS. DRAIN CURRENT (TYPICAL)



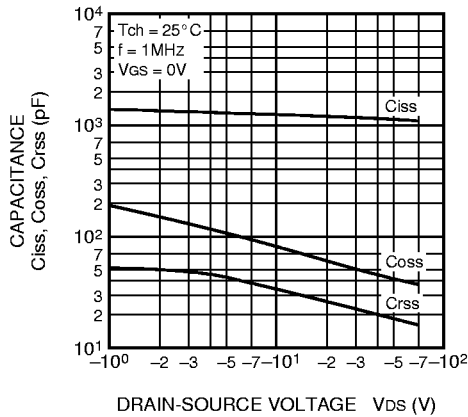
TRANSFER CHARACTERISTICS (TYPICAL)



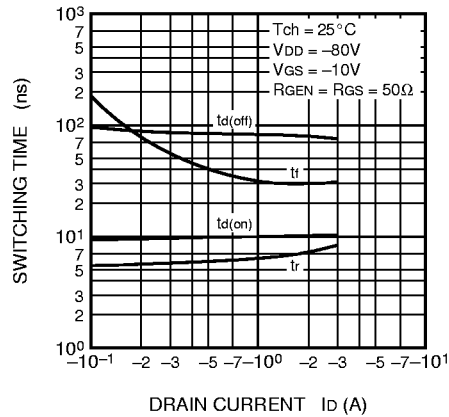
FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT (TYPICAL)



CAPACITANCE VS. DRAIN-SOURCE VOLTAGE (TYPICAL)

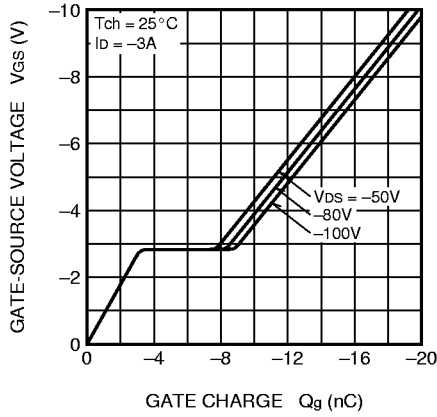


SWITCHING CHARACTERISTICS (TYPICAL)

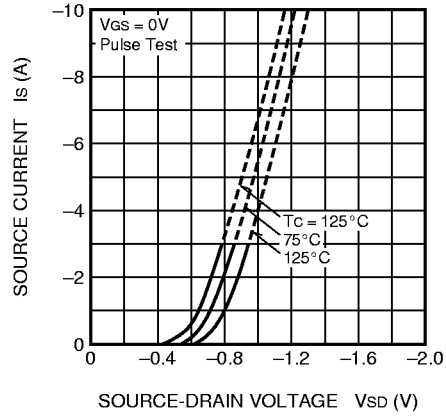


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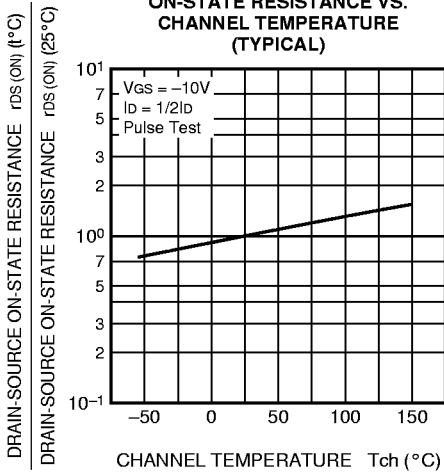
GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)



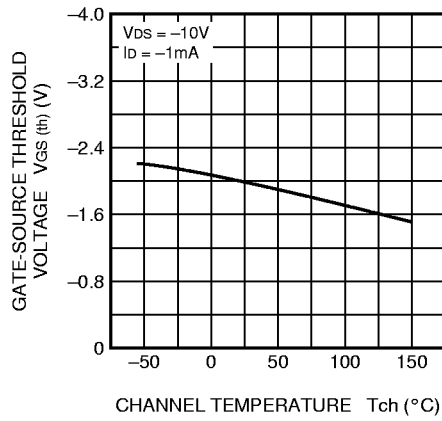
SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)



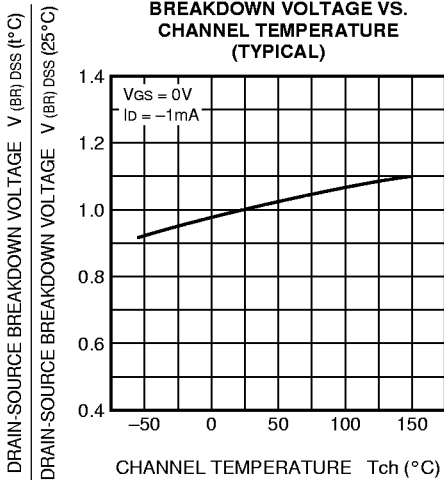
ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)



THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS

